Wideband silicon germanium low-noise amplifier MMIC

Rev. 01 — 2 March 2009

**Product data sheet** 

## 1. Product profile

## 1.1 General description

The BGU7003 MMIC is a wideband amplifier in SiGe:C technology for high speed, low-noise applications in a plastic, leadless 6 pin, extremely thin small outline SOT891 package.

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

### 1.2 Features

- Low noise high gain microwave MMIC
- Applicable between 40 MHz and 6 GHz
- Integrated temperature stabilized bias for easy design
- Bias current configurable with external resistor
- Noise figure NF = 0.80 dB at 1.575 GHz
- Insertion power gain = 18.3 dB at 1.575 GHz
- 110 GHz transit frequency SiGe:C technology
- Power-down mode current consumption < 1 μA</p>
- Optimized performance at low 5 mA supply current
- ESD protection > 1 kV Human Body Model (HBM) on all pins

### 1.3 Applications

- GPS
- Satellite radio
- Low-noise amplifiers for microwave communications systems
- WLAN and CDMA applications
- Analog / digital cordless applications



# **BGU7003**

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## 1.4 Quick reference data

#### Table 1.Quick reference data

 $T_{amb} = 25 \text{ °C}; V_{CC} = 2.5 \text{ V}; I_{CC(tot)} = 5.0 \text{ mA}; V_{ENABLE} \ge 0.7 \text{ V}; f = 1575 \text{ MHz}; Z_S = Z_L = 50 \Omega$  (input and output matched to 50  $\Omega$ ) unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage	RF input AC coupled		2.2	-	2.85	V
I <sub>CC(tot)</sub>	total supply current	configurable with external resistor	[1]	3	-	15	mA
T <sub>amb</sub>	ambient temperature			-40	+25	+85	°C
P <sub>tot</sub>	total power dissipation	$T_{sp} \le 103 \ ^{\circ}C$	[2]	-	-	70	mW
s <sub>21</sub>   <sup>2</sup>	Insertion power gain			-	18.3	-	dB
NF	noise figure			-	0.80	-	dB
P <sub>i(1dB)</sub>	input power at 1 dB gain compression			-	-20.1	-	dBm
IP3 <sub>I</sub>	input third-order intercept point	jammers at $f_1 = f + 138$ MHz and $f_2 = f + 276$ MHz		-	-0.2	-	dBm

 $\label{eq:II} [1] \quad I_{CC(tot)} = I_{CC} + I_{RF\_OUT} + I_{R\_BIAS}.$ 

[2]  $T_{sp}$  is the temperature at the solder point of the ground lead.

## 2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	R_BIAS		
2	RF_IN		$\overset{5}{\sim}$
3	GND		2 - 4
4	RF_OUT		
5	ENABLE		1 3 sym128
6	V <sub>CC</sub>	6 5 4 bottom view	

# 3. Ordering information

Table 3.         Ordering information						
Type number	Package					
	Name	Description	Version			
BGU7003	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1 \times 0.5$ mm	SOT891			

## 4. Marking

Table 4.         Marking codes	
Type number	Marking code
BGU7003	B3

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## 5. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage	RF input AC coupled		-	3.0	V
I <sub>CC(tot)</sub>	total supply current	configurable with external resistor		-	25	mA
P <sub>tot</sub>	total power dissipation	$T_{sp} \le 103 \ ^{\circ}C$	[1]	-	70	mW
T <sub>stg</sub>	storage temperature			-65	+150	°C
Ti	junction temperature			-	150	°C

[1]  $T_{sp}$  is the temperature at the solder point of the ground lead.

## 6. Thermal characteristics

Table 6.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		235	K/W

## 7. Characteristics

#### Table 7. Characteristics

 $T_{amb} = 25 \circ C$ ;  $V_{CC} = 2.5 V$ ;  $I_{CC(tot)} = 5.0 mA$ ;  $V_{ENABLE} \ge 0.7 V$  unless otherwise specified. All measurements done on characterization board without matching, de-embedded up to the pins.

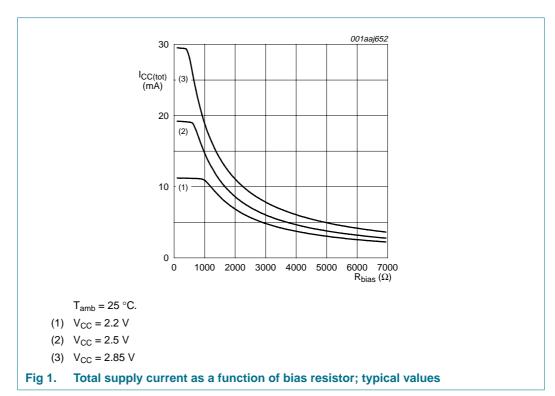
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage	RF input AC coupled		2.2	-	2.85	V
I <sub>CC(tot)</sub>	total supply current	configurable with external resistor	[1]	3	-	15	mA
		$V_{\text{ENABLE}} \leq 0.4 \text{ V}$	[1]	-	-	0.001	mA
T <sub>amb</sub>	ambient temperature			-40	+25	+85	°C
s <sub>21</sub>   <sup>2</sup>	insertion power gain	T <sub>amb</sub> = 25 °C					
		f = 1.575 GHz		16.0	17.5	-	dB
		f = 2.4 GHz	[2]	14.0	15.2	-	dB
		f = 5.8 GHz	[2]	10.0	11.4	-	dB
		$-40~^\circ C \leq T_{amb} \leq 85~^\circ C$					
		f = 1.575 GHz	[2]	15.0	17.5	-	dB
		f = 2.4 GHz	[2]	13.0	15.2	-	dB
		f = 5.8 GHz	[2]	9.0	11.4	-	dB
MSG	maximum stable gain	f = 1.575 GHz		-	20.5	-	dB
		f = 2.4 GHz		-	17.8	-	dB
		f = 5.8 GHz		-	15.4	-	dB
NF <sub>min</sub>	minimum noise figure	f = 1.575 GHz		-	0.70	-	dB
		f = 2.4 GHz		-	0.80	-	dB
		f = 5.8 GHz			1.5		dB

 $[1] \quad I_{CC(tot)} = I_{CC} + I_{RF_{OUT}} + I_{R_{BIAS}}.$ 

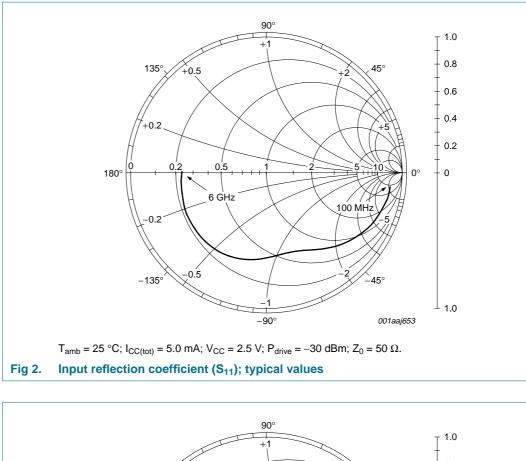
[2] Guaranteed by design and characterization.

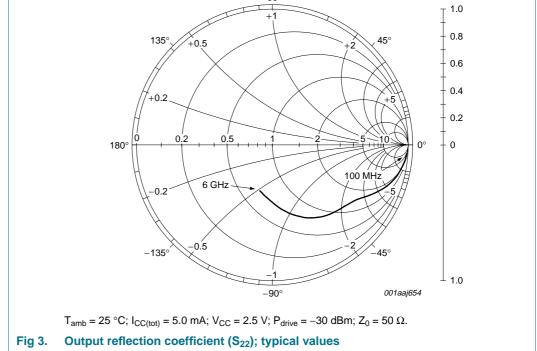
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-40 °C $\leq T_{amb} \leq$ +85 °C		
V <sub>ENABLE</sub> (V)	State	
≤ 0.4	OFF	
≥ 0.7	ON	

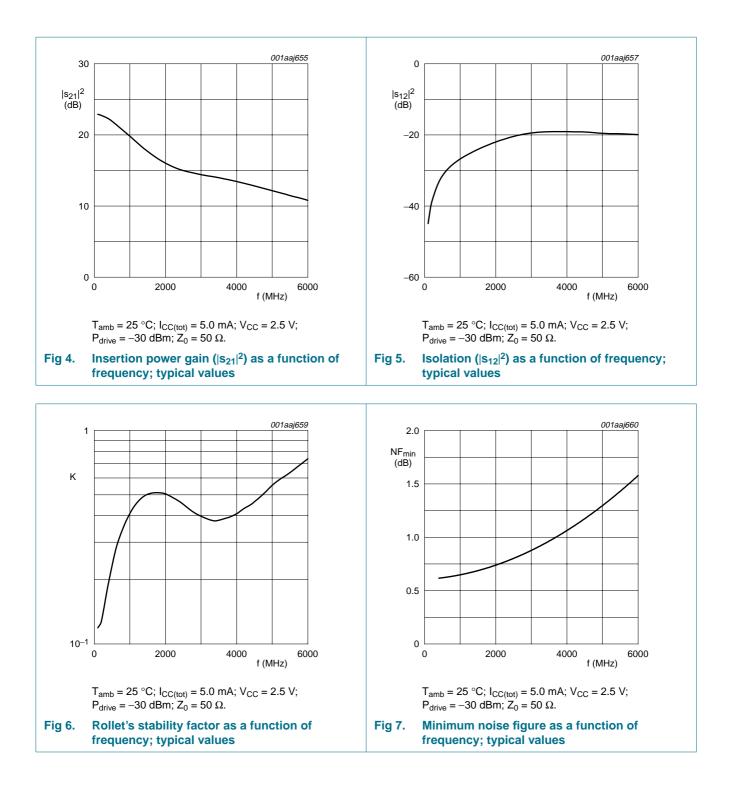


#### ENABLE (pip 5) Table 9

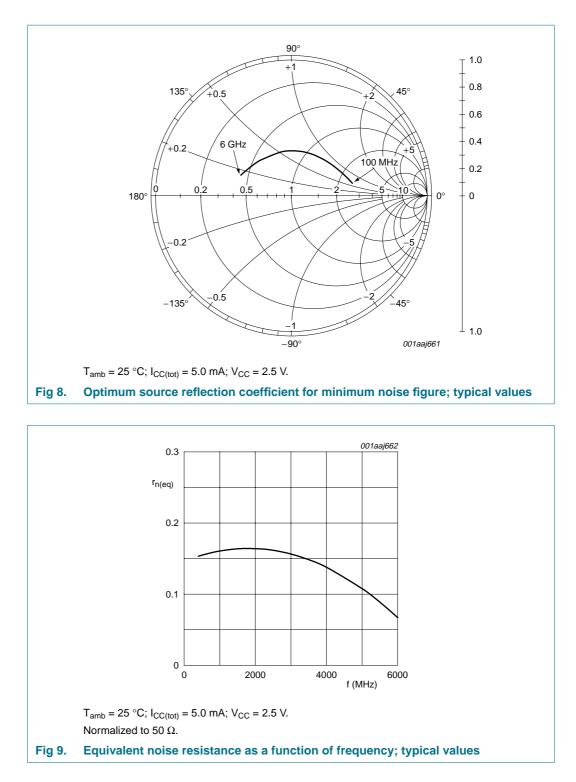




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### Wideband silicon germanium low-noise amplifier MMIC



## 8. Application information GPS LNA

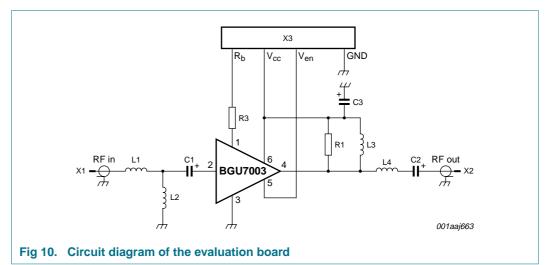
Other applications available. Please contact your local sales representative for more information. Application note(s) available on the NXP website.

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#### Wideband silicon germanium low-noise amplifier MMIC

## 8.1 Application circuit

In Figure 10 the application diagram as supplied on the evaluation board is given.



# Table 9.List of componentsFor circuit, see Figure 10.

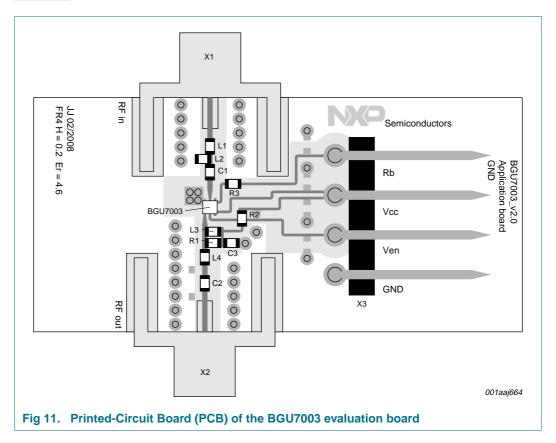
Component	Description	Value		Supplier name/type	Remarks
C1, C2	capacitor	100 pF	[1]	MurataGRM1555	DC blocking
C3	capacitor	180 pF	[1]	MurataGRM1555	decoupling
L1	inductor	2.7 nH	[1]	Murata/LQW15A high quality factor, low series resistance	input matching
L2	inductor	33 nH	<u>[1]</u>	Murata/LQW15A high quality factor, low series resistance	input matching
L3	inductor	3.9 nH	<u>[1]</u>	Murata/LQG15HS	output matching / DC shunt
L4	inductor	4.7 nH	<u>[1]</u>	Murata/LQG15HS	output matching
R1	resistor	180 Ω	[1]		
R2	resistor	0 Ω	[1]		bridge
R3	resistor	$3300 \ \Omega$	[1]		bias setting
X1, X2	SMA RF connector	-		Johnson, end launch SMA 142-0701-841	RF input / RF output
Х3	DC header	-		Molex, PCB header, right angle, 1 row, 4 way 90121-0764	bias connector

[1] all capacitors, inductors and resistors have 0402 footprint.

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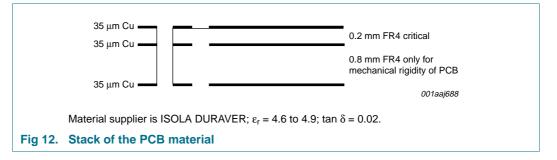
### 8.2 Application board layout

Figure 11 shows the board layout with component identifications.



### 8.3 Printed-Circuit Board

The material that has been used for the evaluation board is FR4 using the stack shown in Figure 12.



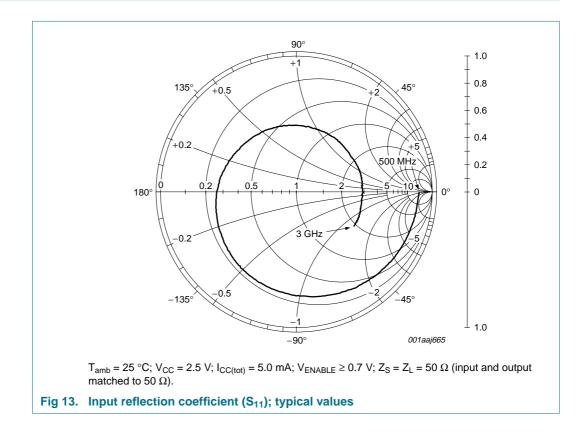
#### Wideband silicon germanium low-noise amplifier MMIC

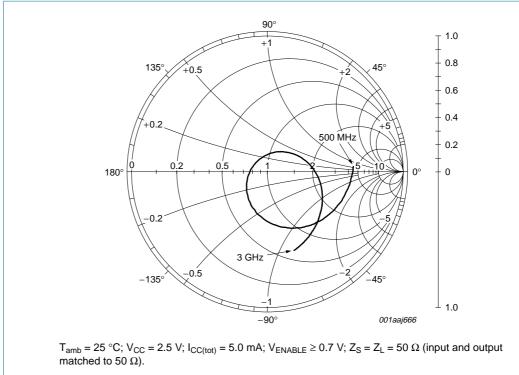
### 8.4 GPS evaluation board

#### Table 10. GPS application characteristics

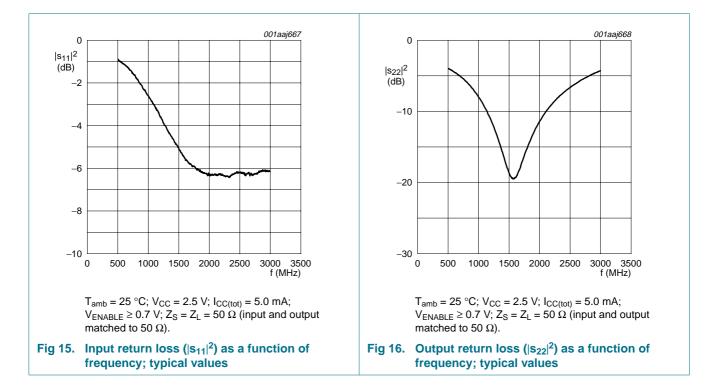
 $T_{amb} = 25 \degree C$ ;  $V_{CC} = 2.5 V$ ;  $I_{CC(tot)} = 5.0 \text{ mA}$ ; f = 1.575 GHz;  $V_{ENABLE} \ge 0.7 V$ ;  $Z_S = Z_L = 50 \Omega$  (input and output matched to 50  $\Omega$ ) unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
s <sub>21</sub>   <sup>2</sup>	Insertion power gain		-	18.3	-	dB
S <sub>11</sub>   <sup>2</sup>	input return loss		-	-5.4	-	dB
S <sub>22</sub>   <sup>2</sup>	output return loss		-	-19.5	-	dB
S <sub>12</sub>   <sup>2</sup>	isolation		-	-24.6	-	dB
NF	noise figure		-	0.80	-	dB
P <sub>i(1dB)</sub>	input power at 1 dB gain compression		-	-20.1	-	dBm
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		-	-2.8	-	dBm
IP3 <sub>I</sub>	input third-order intercept point	jammers at $f_1 = f + 138$ MHz and $f_2 = f + 276$ MHz	-	-0.2	-	dBm
		$f_1 = f + 5 \text{ MHz}; f_2 = f + 10 \text{ MHz}$	-	-5.2	-	dBm



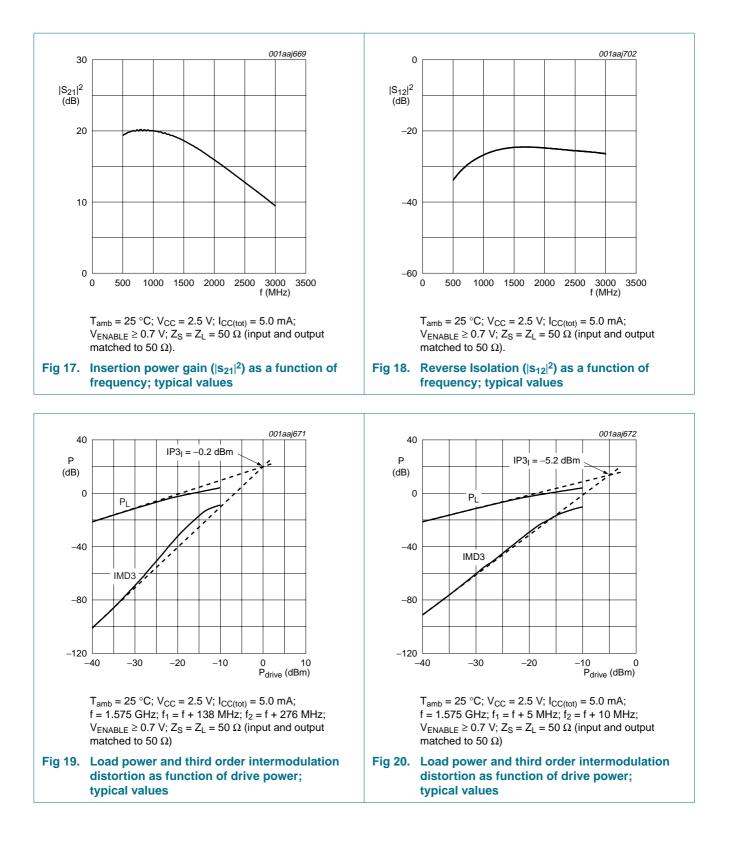






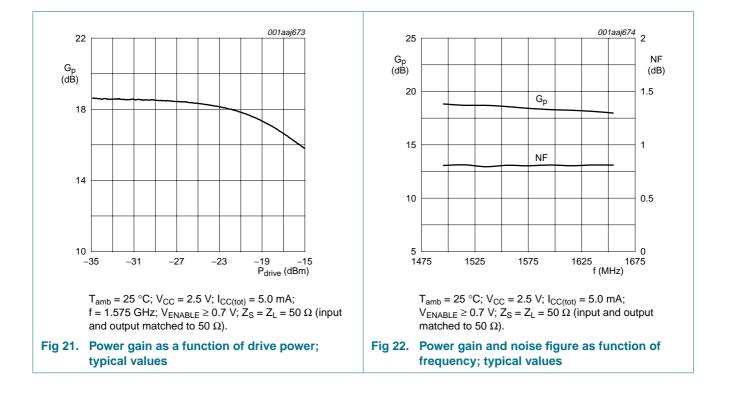
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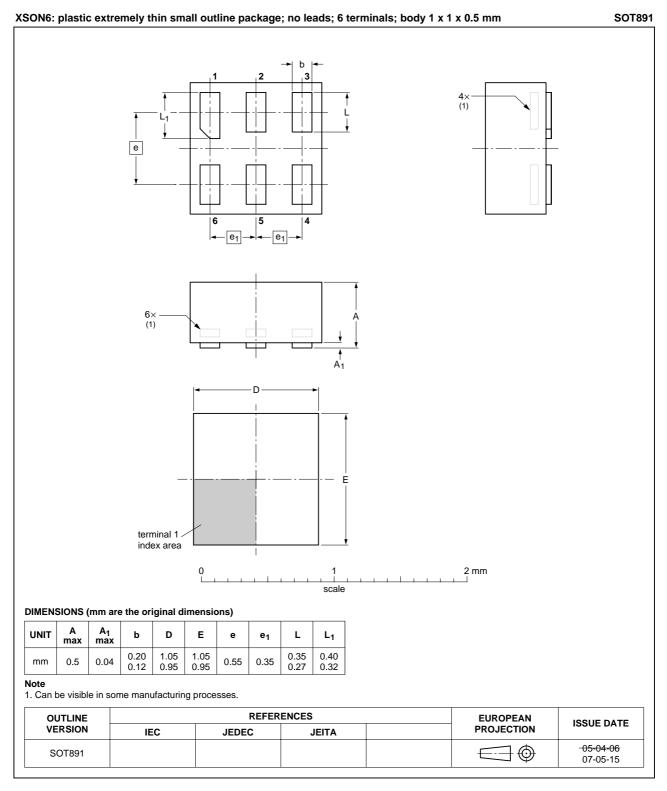
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# **BGU7003**



### Wideband silicon germanium low-noise amplifier MMIC

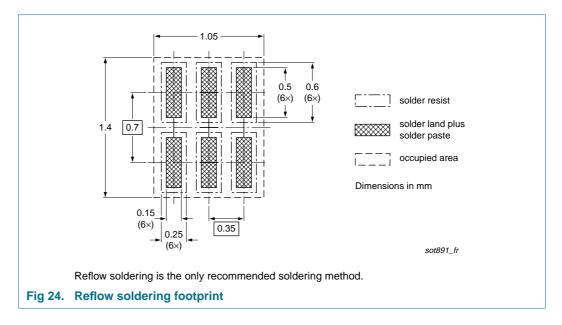
## 9. Package outline



### Fig 23. Package outline SOT891 (XSON6)

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## **10. Soldering**



## **11. Abbreviations**

Acronym	Description
AC	Alternating Current
CDMA	Code Division Multiple Access
DC	Direct Current
FR4	Flame Retardant 4
GPS	Global Positioning System
LNA	Low-Noise Amplifier
MMIC	Monolithic Microwave Integrated Circuit
RF	Radio Frequency
SiGe:C	Silicon Germanium Carbon
SMA	SubMiniature version A
WLAN	Wireless Local Area Network

## 12. Revision history

Table 12. Revision histo	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU7003_1	20090302	Product data sheet	-	-

## **13. Legal information**

### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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